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<b>IN THE UNITED STATES PATENT AND TRADEMARK OFFICE</b>	<i>Application No.</i>	10/024,475
	<i>Filing Date</i>	December 21, 2001
	<i>First Named Inventor</i>	Chan-ho PARK
	<i>Group Art Unit</i>	2811
	<i>Examiner Name</i>	Ori Nadav
	<i>Attorney Docket No.</i>	1751-294
<i>Title of the Invention:</i> <b>HIGH VOLTAGE SEMICONDUCTOR DEVICE HAVING HIGH BREAKDOWN VOLTAGE AND METHOD OF FABRICATING THE SAME</b>		

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**RESPONSE TO RESTRICTION REQUIREMENT**

Assistant Commissioner for Patents  
Washington, D.C. 20231

Dear Sir:

In response to the restriction requirement mailed August 23, 2002, Applicant hereby elects Group I, consisting of claims 1-3, drawn to a semiconductor device, classified in class 257, subclass 341. Applicant reserves the right to pursue the non-elected claims in a divisional application.

Favorable action on the elected claims is earnestly solicited.

<b>RESPECTFULLY SUBMITTED,</b>					
<b>NAME AND REG. NUMBER</b>	Monica S. Davis, Registration No. 44,492				
<b>SIGNATURE</b>			<b>DATE</b>	9-16-02	
<b>Address</b>	Rothwell, Figg, Ernst & Manbeck 1425 K Street, N.W., Suite 800				
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